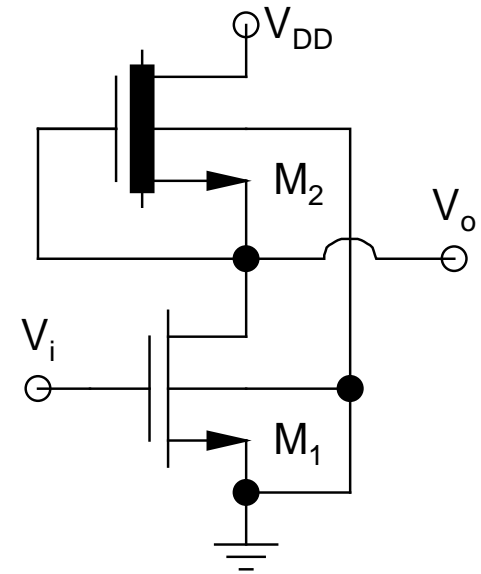


- **Depletion Load:**

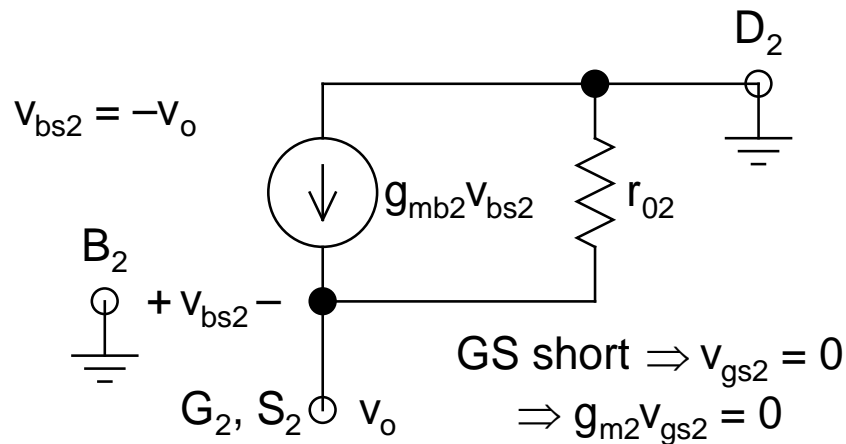
- $M_2$  is *depletion mode*, having *negative*  $V_{TN0}$  (*denoted by*  $V_{TD0}$ )
- *Back bias of*  $M_2$ :  
 $V_{SB2} = V_o$
- *With*  $V_o$ ,  $V_{TD2}$  *changes*
- *Maximum*  $V_o$  *desired*  $= V_{DD}$
- *This is also the maximum back bias of*  $M_2$



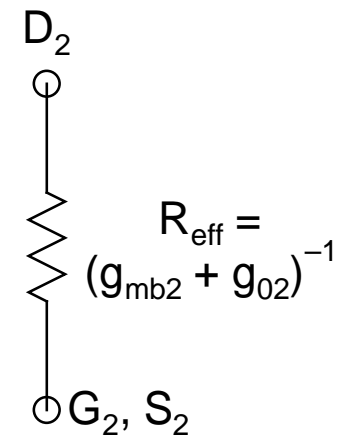
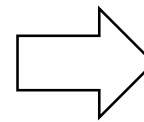
**Circuit Schematic**

- *$M_2$  has GS short  $\Rightarrow V_{GS2} = 0$*
- *Even with  $V_o = V_{SB2}(max) = V_{DD}$ ,  $V_{TD2}$  should remain negative with a cushion of at least 100 mV*
  - $\Rightarrow V_{TD2}$  with  $V_{SB2} = V_{DD}$  should be -100 mV
  - $\Rightarrow V_{TD0}$  should be chosen based on this
- Now,  *$V_{DS2}(min) = V_{DD} - V_o(max) = 0$*
- Under this condition,  *$V_{GS2} - V_{TD2} = \Delta V_2 = 100$  mV*
  - $\Rightarrow M_2$  is in the linear region (*since  $V_{DS2} < \Delta V_2$* )

- *This has to be lived with*, and *slight distortion would appear at the output as  $V_o \rightarrow V_{DD}$*
- For *best biasing*,  $V_{oQ} = V_{DD}/2$   
 $\Rightarrow$  *Fixes the DC operating point*
- Before doing *ac analysis*, *let's investigate  $M_2$* :



ac Midband Equivalent of  $M_2$



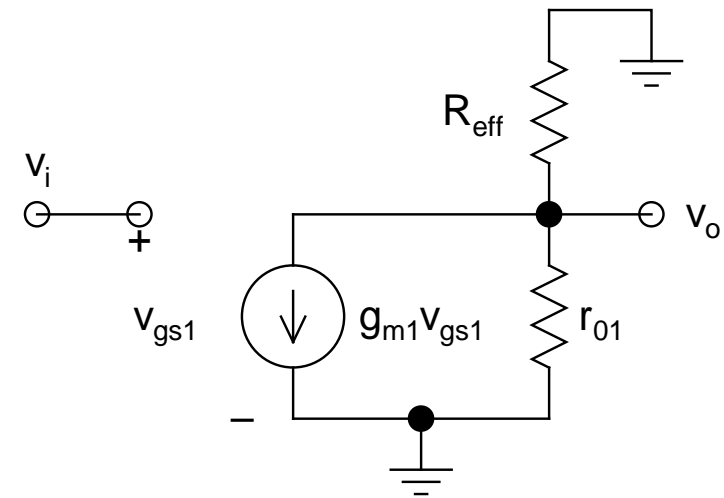
Simplified Equivalent

➤ Thus, the **complete equivalent**:

➤ **By inspection**:

$$A_v = \frac{V_o}{V_i} = -g_{m1} (r_{o1} \parallel R_{\text{eff}})$$

$$= -\frac{g_{m1}}{g_{mb2} + g_{o1} + g_{o2}}$$



➤ Now, in general,

$$g_{mb2} \gg (g_{o1} + g_{o2})$$

$$\Rightarrow A_v \approx -\frac{g_{m1}}{g_{mb2}} = -\frac{g_{m1}}{\chi_2 g_{m2}} = -\frac{1}{\chi_2} \sqrt{\frac{(W/L)_1}{(W/L)_2}}$$

**Complete Equivalent**

$$\chi_2 = \frac{\gamma}{2\sqrt{2\phi_F + V_{DD}/2}} < 1$$

$\Rightarrow$  **Improvement** as compared to previous stage

➤ Now, if  $M_2$  can be put in its *separate island*, then  *$S_2$  and  $B_2$  can be connected together*

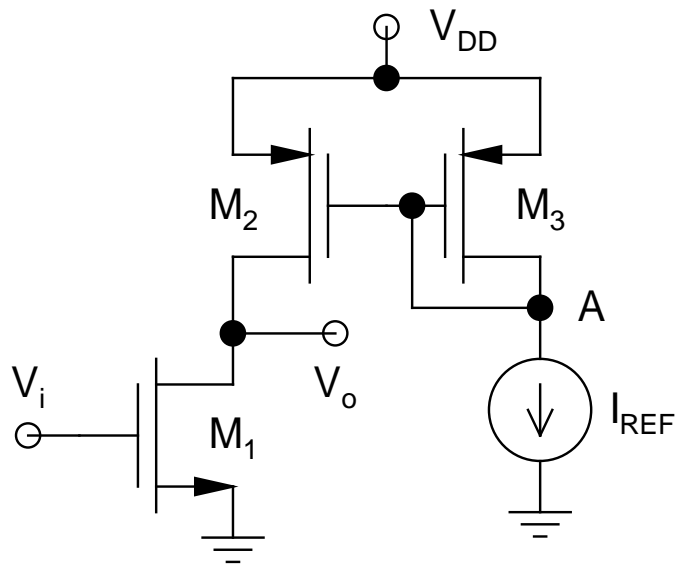
$$\Rightarrow v_{sb2} = 0 \Rightarrow g_{mb2}v_{sb2} = 0$$

$$\Rightarrow A_v = -\frac{g_{m1}}{g_{01} + g_{02}}$$

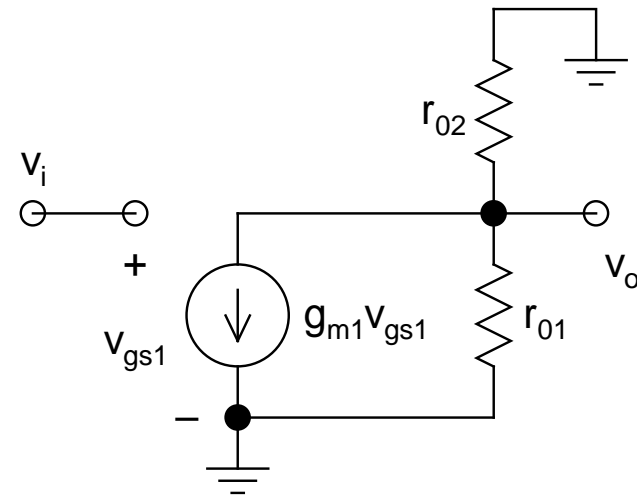
- Can be *very large* (*a magnitude greater than 100 is possible*)

- $R_0 = (g_{mb2} + g_{01} + g_{02})^{-1}$  (*with body effect*)
- $R_0 = (g_{01} + g_{02})^{-1}$  (*without body effect*)
- The latter case produces *very high*  $R_0$
- Thus, this circuit produces *much superior performance* as compared to the *saturated enhancement load*, in terms of:
  - *Rail-to-rail swing*
  - *With island technology:*
    - ❖ *Very large  $A_v$  and  $R_0$*
  - *Without island technology:*
    - ❖ *Moderate  $A_v$  and  $R_0$*

- ***Complementary PMOS Load:***
  - Also known as ***CMOS Gain Stage***
    - ***CMOS*** (***Complementary MOS***: ***Having both NMOS and PMOS*** in the circuit)
  - ***The Ultimate: Much superior performance*** and ***outclasses all other gain stages***
  - ***Widely used***
  - ***High  $A_v$  and  $R_0$***
  - ***Easy to bias and easy to operate***
  - ***Design also extremely simple***
  - ***Doesn't produce any anomalies***



**Circuit Schematic**



**ac Midband Equivalent**

- *$M_1$  body connected to ground,  $M_2$ - $M_3$  bodies connected to  $V_{DD}$* 
  - *No body effect problem for any of the devices (biggest advantage of this circuit)*